

SANYO	No.2265A	2SB1269/2SD1905
		PNP/NPN Epitaxial Planar Type Silicon Transistors HIGH-CURRENT SWITCHING APPLICATIONS

Applications

- . Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications

Features

- . Suitable for sets whose height is restricted
- . Low collector to emitter saturation voltage
- . Wide ASO and highly resistant to breakdown

(): 2SB1269

Absolute Maximum Ratings at Ta=25°C

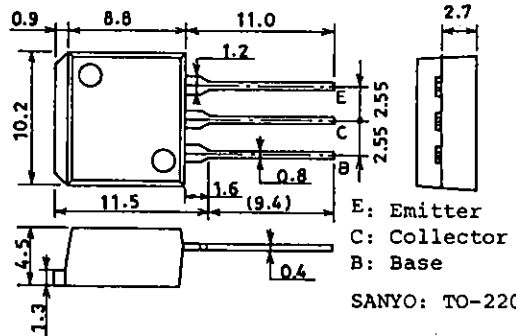
			unit
Collector to Base Voltage	V _{CB0}	(-)60	V
Collector to Emitter Voltage	V _{CEO}	(-)50	V
Emitter to Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)7	A
Peak Collector Current	i _{cp}	(-)12	A
Collector Dissipation	P _C	1.65	W
	T _c =25°C	40	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I _{CB0} V _{CB} =(-)40V, I _E =0			(-)0.1	mA
Emitter Cutoff Current	I _{EBO} V _{EB} =(-)4V, I _C =0			(-)0.1	mA
DC Current Gain	h _{FE} (1) V _{CE} =(-)2V, I _C =(-)1A	70*		280*	
	h _{FE} (2) V _{CE} =(-)2V, I _C =(-)5A	30			
Gain-Bandwidth Product	f _T V _{CE} =(-)5V, I _C =(-)1A		10		MHz
C-E Saturation Voltage	V _{CE(sat)} I _C =(-)4A, I _B =(-)0.4A			(-)0.4	V
C-B Breakdown Voltage	V _{(BR)CBO} I _C =(-)1mA, I _E =0	(-)60			V
C-E Breakdown Voltage	V _{(BR)CEO} I _C =(-)1mA, R _{BE} =∞	(-)50			V
E-B Breakdown Voltage	V _{(BR)EBO} I _E =(-)1mA, I _C =0	(-)6			V

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Package Dimensions 2049B
(unit: mm)



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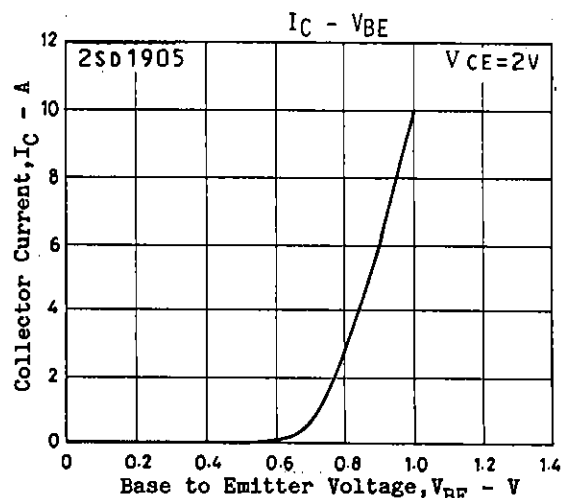
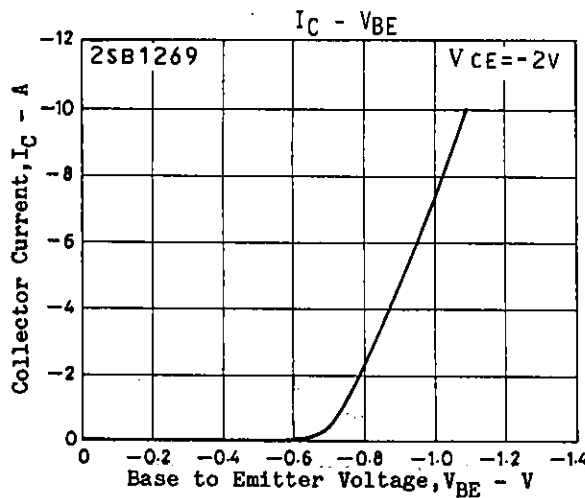
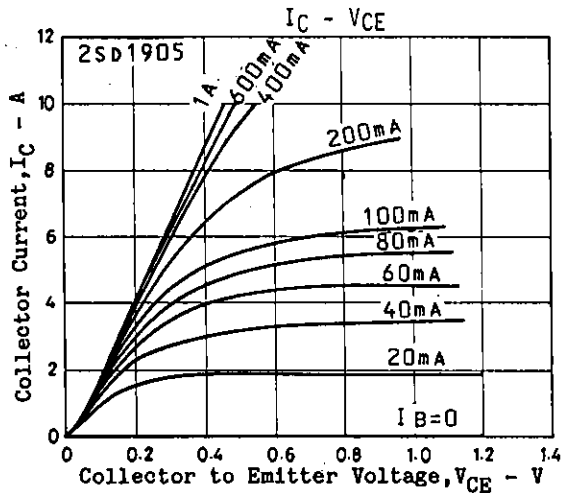
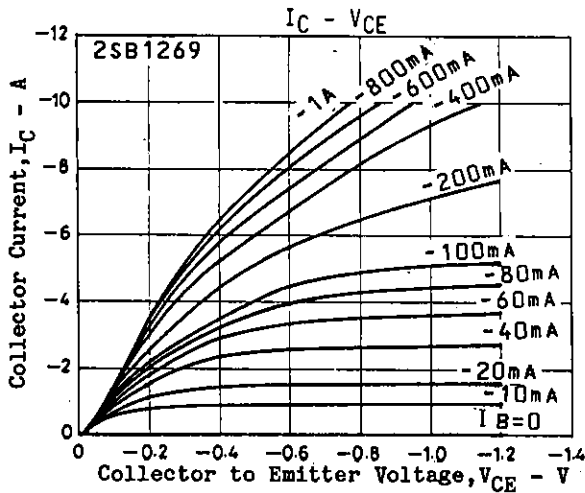
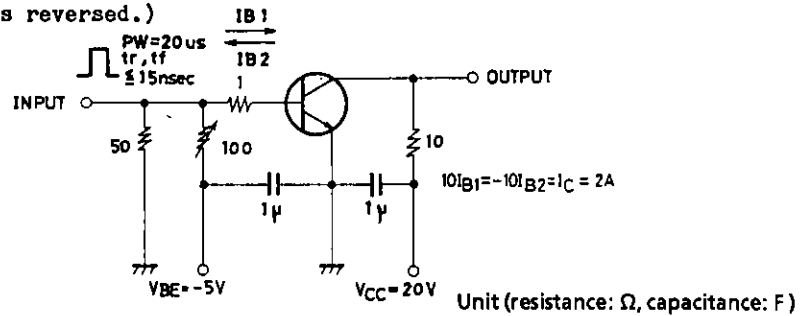
			min	typ	max	unit
Turn-on Time	t_{on}	See specified Test Circuit.		0.2		μs
Storage Time	t_{stg}	"	(0.1)	0.3		μs
Fall Time	t_f	"	(0.7)	0.9		μs

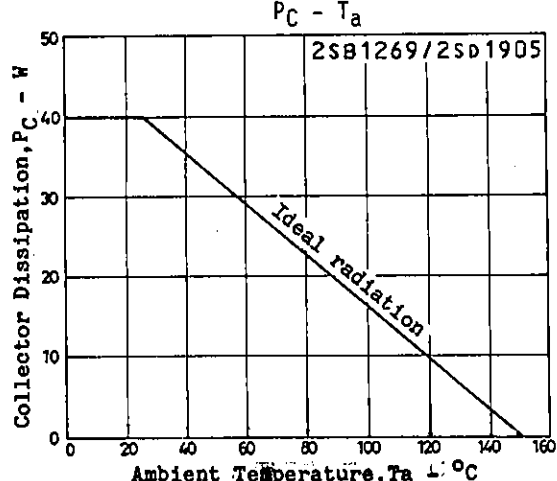
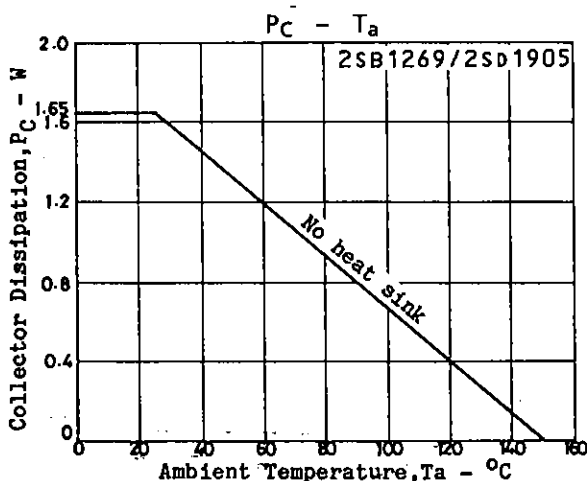
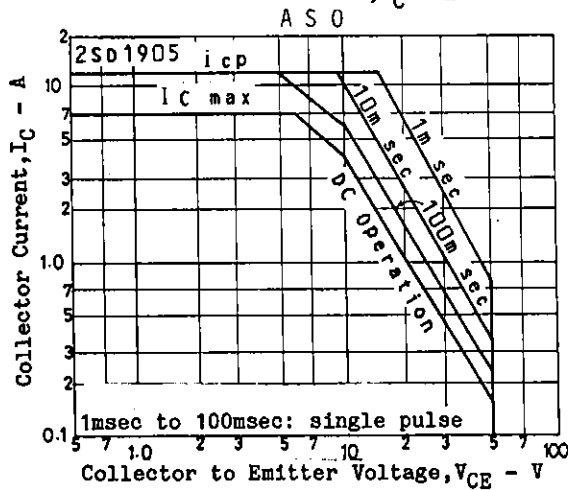
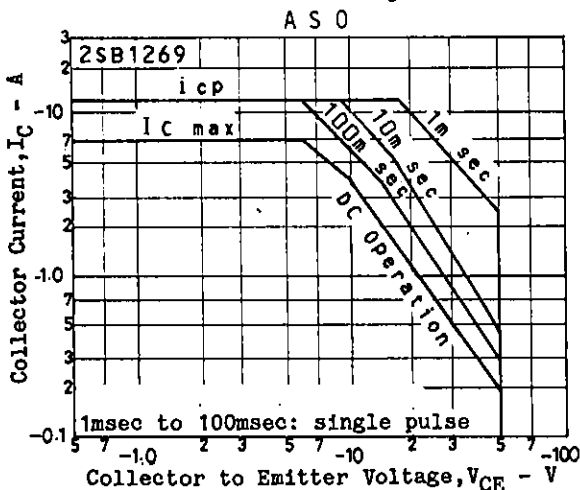
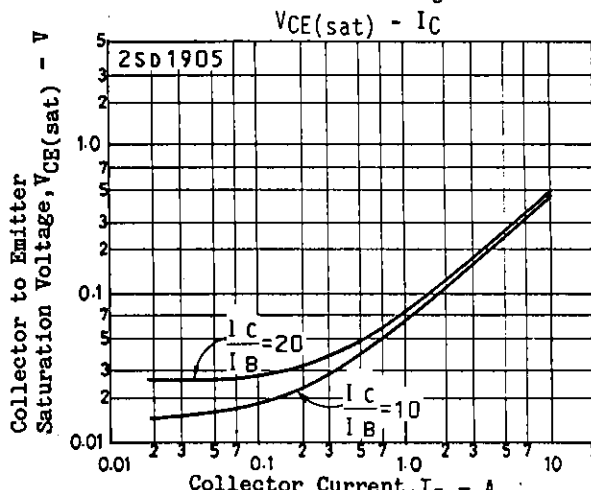
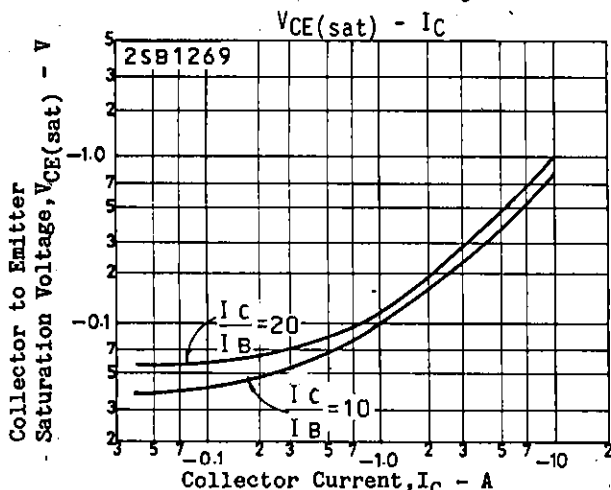
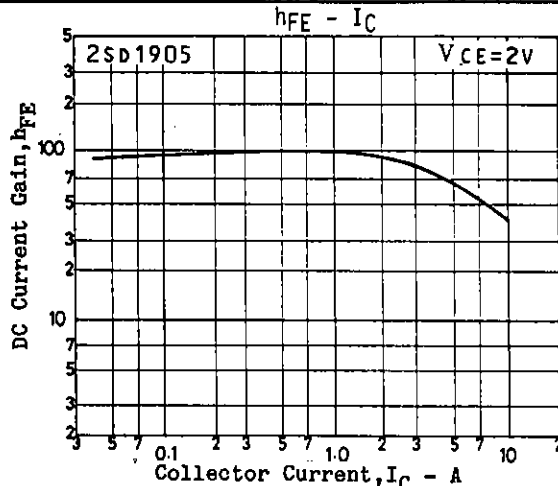
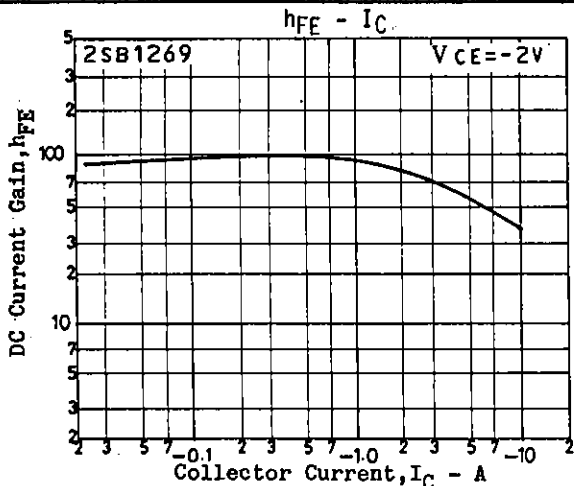
*: The 2SB1269/2SD1905 are classified by 1A h_{FE} as follows:

70 Q 140	100 R 200	140 S 280
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Switching Time Test Circuit

(For PNP, the polarity is reversed.)





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